

30BQ040

Technical Data Data Sheet N0674, Rev. - **Green Products**

30BQ040 SCHOTTKY RECTIFIER

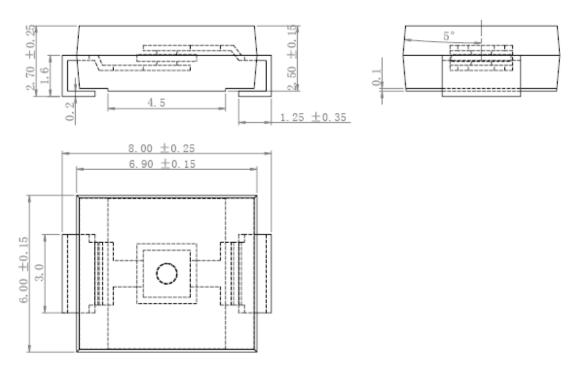
Applications:

- Disk Drives
- Switching power supply
- Redundant power subsystems
- Converters
- Free-Wheeling diodes
- Reverse battery protection
- Battery Charging

Features:

- Small foot print, surface moutable
- Low forward voltage drop
- High frequency operation
- Guard ring for enhanced ruggedness and long term reliability
- This is a Pb Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

Mechanical Dimensions (In mm / Inches):



SMC

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FAX (86) 25-87123900 • World Wide Web Site - http://www.sangdest.com.cn • E-Mail Address - sales@ sangdest.com.cn •</sup>



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Where XXXXX is YYWWL

SC3F	= Part Name
YY	= Year
WW	= Week
L	= Lot Number

Cautions: Molding resin Epoxy resin UL:94V-0

Ordering Information:

Device	Package	Shipping
30BQ040	SMC (Pb-Free)	3000pcs / reel

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification.

Maximum Ratings:

Characteristics	Symbol	Condition	Max.	Units
Peak Inverse Voltage	V _{RWM}	-	40	V
Max. Average Forward Current	I _{F(AV)}	50% duty cycle @T _c =118°C, rectangular wave form	3.0	А
Max. Peak One Cycle Non- Repetitive Surge Current	I _{FSM}	8.3 ms, half Sine pulse	132	A



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Electrical Characteristics:

Characteristics	Symbol	Condition	Max.	Units
Max. Forward Voltage Drop*	V _{F1}	@ 3 A, Pulse, T _J = 25 °C	0.53	V
		@ 6 A, Pulse, T _J = 25 °C	0.68	
	V _{F2}	@ 3 A, Pulse, T _J = 125 °C	0.43	V
		@ 6 A, Pulse, T _J = 125°C	0.57	
Max. Reverse Current *	I _{R1}	$@V_R = Rated V_R$, Pulse,	0.5	mA
		T _J = 25 °C		
	I _{R2}	$@V_R = Rated V_R$, Pulse,	30	mA
		T _J = 125 °C		
Max. Junction Capacitance	Ст	@V _R = 5V, T _C = 25 °C	230	PF
		f _{SIG} = 1MHz		
Typical Series Inductance	Ls	Measured lead to lead 5 mm from	3.0	nH
		package body		
Max. Voltage Rate of	dv/dt	-	10,000	V/µs
Change				

 * Pulse Width < 300 μ s, Duty Cycle < 2%

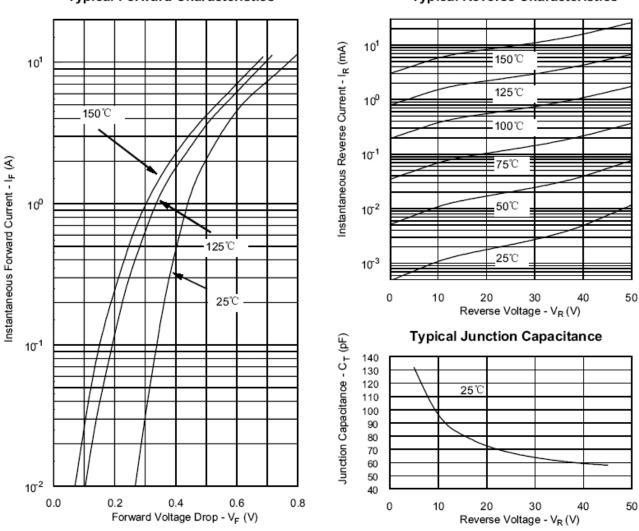
Thermal-Mechanical Specifications:

Characteristics	Symbol	Condition	Specification	Units
Max. Junction Temperature	ТJ	-	-55 to +150	С°
Max. Storage Temperature	T _{stg}	-	-55 to +150	С°
Maximum Thermal Resistance Junction to Lead	$R_{ ext{ heta}JL}$	DC operation	12	°C/W
Maximum Thermal Resistance Junction to Case	$R_{ ext{ heta}JA}$	DC operation	46	°C/W
Approximate Weight	wt	-	0.65	g
Case Style	SMC			

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Typical Forward Characteristics

Typical Reverse Characteristics

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